

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	(semiconductor adj memory) and (((cut or blow or stop) with (power or supply or voltage)) with (before adj2 test\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/27 12:59
L2	0	(semiconductor adj memory) and (((cut or blow or stop) with (power or supply or voltage)) with ("not selected" with test\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/27 13:00
S1	1	10/802210	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/03 09:39
S2	9871	test\$3 WITH (memory ADJ cell)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/03 09:39
S3	39	(test\$3 WITH (memory ADJ cell)) WITH (switch\$3 NEAR (voltage OR power))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/03 12:20
S4	14	urick.XA.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/03 09:54
S5	0	S4 AND JTAG	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/03 10:04
S6	1	10/802210	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/03 10:04

S7	1	S6 AND cell	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/03 10:19
S8	3	((("6425101") or ("6611518") or ("5710550")).PN.	USPAT; USOCR	OR	OFF	2007/01/03 10:19
S9	13	("5282271" "5319261" "5359592" "5406138" "5428750" "5428800" "5465056").PN. OR ("5710550").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/01/03 10:26
S10	14	"934666"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/03 12:07
S11	3	S10 AND sato.IN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/03 12:07
S12	919	(memory ADJ cell) WITH (switch\$3 NEAR (voltage OR power))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/03 12:21
S13	488	S12 AND (row WITH column)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/03 12:20
S14	35	((row OR column OR grid OR crosspoint OR crossbar) NEAR2 (memory ADJ cell)) WITH (switch\$3 NEAR (voltage OR power))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/03 13:22
S15	2	"4639895".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/03 13:07

S16	2	S15 AND (row OR column)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/03 13:07
S17	77	(crosspoint OR crossbar OR (cross ADJ point) OR (cross ADJ bar)) NEAR switch\$3 WITH (memory NEAR cell)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/03 13:42
S18	564	(memory ADJ cells) WITH (row\$1 NEAR column\$1) SAME fuse	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/03 13:45
S19	564	(memory ADJ cell\$1) WITH (row\$1 NEAR column\$1) SAME fuse	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/03 13:47
S20	181	(memory ADJ cell\$1) WITH (row\$1 NEAR column\$1) SAME (test\$3 AND fuse)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/03 13:46
S21	97	((memory ADJ cell\$1) WITH (row\$1 NEAR column\$1) SAME fuse).AB.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/03 13:56
S22	728	714/710,711.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/03 13:57
S23	417	S22 AND (row\$1 AND column\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/03 13:57
S24	60	S23 AND (test\$3 WITH volt \$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/03 13:58

S25	18	("4354217" "4392211" "4473895").PN. OR ("4639895").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/01/03 16:43
S26	1	"5703816".pn.	US-PGPUB; USPAT; USOCR	OR	ON	2007/01/03 16:43
S27	1	S26 AND (row WITH column)	US-PGPUB; USPAT; USOCR	OR	ON	2007/01/03 16:43
S28	101	S23 AND ((blow\$3 OR cut \$4) ADJ fuse)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 11:04
S29	79	S28 NOT S24	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/04 09:32
S30	2	"4,672,581".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/03 17:32
S31	2	"20020167849"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/03 17:45
S32	3	((("5390150") or ("5703816") or ("6456547")).PN.	USPAT; USOCR	OR	OFF	2007/01/04 08:32
S33	3149	(memory ADJ cell) NEAR (row WITH column)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/04 09:33
S34	4865	(memory ADJ cell) NEAR (row NEAR2 column)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/04 09:33
S35	7	S33 SAME ((blow\$3 OR cut \$4) ADJ fuse)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/04 09:41

S36	181	S33 AND ((blow\$3 OR cut\$4) ADJ fuse)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/04 09:41
S37	174	S36 NOT S35	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/04 09:41
S40	10214	((blow\$3 OR cut\$4) ADJ fuse)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 11:05
S41	51368	(memory WITH (row AND column))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 11:05
S42	139	(memory WITH (row AND column)) WITH ((blow\$3 OR cut\$4) ADJ fuse)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 11:06
S43	371	(disabl\$3 NEAR precharg\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 13:59
S44	12	(disabl\$3 NEAR precharg\$3) SAME test\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 13:59
S45	14	(pmos NEAR (switch OR transistor)) SAME (test\$3 NEAR memor\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 15:13
S46	56	(power NEAR (switch OR transistor)) SAME (test\$3 NEAR memor\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 15:15

S47	8	((volt\$3 NEAR level) WITH switch) SAME (test\$3 NEAR memor\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 15:16
S48	30	("4543594" "5577050" "5668818" "5764878" "5841709").PN. OR ("5987632").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/01/05 15:27
S49	729	714/710,711.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 15:27
S50	20	S49 AND ((chang\$3 OR switch\$3) WITH (volt\$3 NEAR level))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 15:36
S51	2	S49 AND ((first NEAR second) WITH (volt\$3 NEAR level))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 15:38
S52	0	((voltage NEAR switch) WITH (power NEAR supply)) SAME (memory NEAR test)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 15:39
S53	0	((voltage NEAR switch) WITH (power NEAR supply)) SAME (memory NEAR test)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 15:39
S54	0	((volt\$3 NEAR switch) WITH (power NEAR supply)) SAME (memory NEAR test)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 15:39
S55	2327	((volt\$3 NEAR switch) WITH (power NEAR supply))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 15:40

S56	32178	(DC WITH voltage WITH switch)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 15:41
S57	65	S56 AND (memory NEAR test \$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 15:41
S58	709	voltage ADJ level ADJ switch	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/06 10:23
S59	84	(voltage ADJ level ADJ switch).AB.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/06 10:24
S60	14	(voltage ADJ level ADJ switch) WITH contacts	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/06 10:30
S61	1716	(voltage ADJ source) NEAR switch	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/06 10:31
S62	15	contact\$1 NEAR (voltage ADJ source) NEAR switch	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/06 10:34
S63	118	(voltage ADJ level) NEAR relay	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/06 10:34
S64	1	switching NEAR (voltage ADJ level) NEAR relay	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/06 10:34

S65	10	switching NEAR (voltage ADJ level) WITH relay	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/06 10:36
S66	65	(high AND low) NEAR (voltage ADJ level) WITH (contact OR relay)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/06 10:43
S67	195	(high AND low) NEAR (voltage ADJ switch)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/06 10:43
S68	853	714/42.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/17 09:24
S69	855	714/42.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/17 09:26
S70	546	714/42.ccls. and ("semiconductor memory" or "ram" or "prom" or "eeprom" or "flash memory")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/17 09:25
S71	14	714/42.ccls. and (("semiconductor memory" or "ram" or "prom" or "eeprom" or "flash memory") with repair)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/17 09:27
S75	1169	714/5.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/17 09:27
S76	17	714/5.ccls. and (("semiconductor memory" or "ram" or "prom" or "eeprom" or "flash memory") with repair)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/17 09:27
S77	2426	714/6.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/17 09:32

S78	17	714/6.ccls. and (("semiconductor memory" or "ram" or "prom" or "eeprom" or "flash memory") with repair)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/17 09:33
S79	773	714/7.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/17 10:09
S80	20	714/7.ccls. and (("semiconductor memory" or "ram" or "prom" or "eeprom" or "flash memory") with repair)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/17 10:09
S81	525	714/8.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/17 10:11
S82	13	714/8.ccls. and (("semiconductor memory" or "ram" or "prom" or "eeprom" or "flash memory") with repair)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/17 10:11
S83	1061	714/30.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/17 10:11
S84	16	714/30.ccls. and (("semiconductor memory" or "ram" or "prom" or "eeprom" or "flash memory") with repair)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/17 10:28
S85	68	(SUH-YOUNG-HO SOHN- KYO-MIN).in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/17 10:28
S87	2	"20020167849".did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/17 10:32
S88	35	714/5.ccls. and @pd>="20080117"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/27 08:42

S89	61	714/6.ccls. and @pd>="20080117"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/27 08:52
S90	8	714/7.ccls. and @pd>="20080117"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/27 08:57
S91	9	714/8.ccls. and @pd>="20080117"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/27 08:57
S92	21	714/30.ccls. and @pd>="20080117"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/27 08:59
S93	27	714/42.ccls. and @pd>="20080117"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/27 09:02
S94	309	(semiconductor adj memory) and array and (row or column) and ((cut or blow or stop) with (power or supply or voltage)) and (test with current)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/27 09:47

3/27/08 2:26:35 PM

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